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(a) [forming] a gate dielectric over a semiconductor region;

(b) [forming] a patterned gate over said gate dielectric;

(c) [then performing] a ^{p.b.p}lateral growth [step] on said gate dielectric [to increase the thickness of said gate dielectric] at the corners of said gate, but not under central regions of said gate increasing the thickness of said gate dielectric; ^{pattern}

(d) [depositing] a unitary electrically conductive metallic material entirely covering [onto sidewalls of] said gate; ^{pattern}

(e) reacting said metallic material with said gate to form a conductive compound]; and

(f) [stripping unreacted portions of said metallic material; whereby a gate structure with enhanced conductivity is formed] source and drain regions in said semiconductor region defining a channel under said patterned gate.

[Amend claim 9 as follows:]

9. (Thrice Amended) A [product produced by the method for forming a] transistor gate structure, comprising [the steps of]:

(a) [forming] a gate dielectric over a semiconductor region;

(b) [forming] a patterned gate over said gate dielectric;

(c) [then performing] a lateral growth [step] on said gate dielectric [to increase the thickness of said gate dielectric] at the corners of said gate, but not under central regions of said gate increasing the thickness of said gate dielectric; and ^{pattern}

(d) [after said step (c), forming] a unitary electrically conductive metallic material entirely covering [sidewall spacers on] said gate.

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